

MOTOROLA

TRANSISTORIZED AUDIO OSCILLATOR

MODEL S1067A



MOTOROLA INC.

Communications Division

ENGINEERING PUBLICATIONS

4501 WEST AUGUSTA BOULEVARD

CHICAGO, ILLINOIS 60651

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Issue - A

GUARANTEED PERFORMANCE SPECIFICATIONS

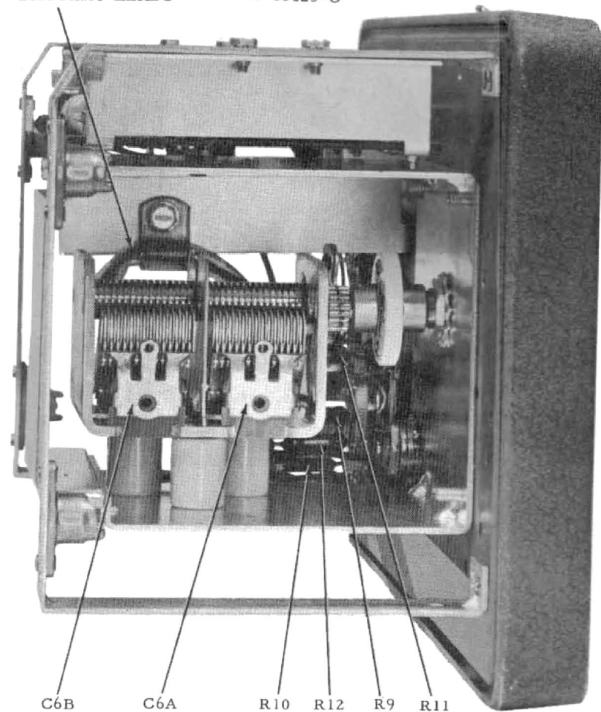
FREQUENCY RANGE	20 cps-200 kc, in 4 overlapping ranges.
DIAL ACCURACY	±5%
FREQUENCY RESPONSE	±1 db into 150 ohms or more (resistive load).
OUTPUT VOLTAGE	1.5 v rms ±1 db into 150 ohms 1.0 v rms (min.) into 50 ohms
SOURCE IMPEDANCE	Less than 50 ohms at any output voltage level.
DISTORTION	less than 1.0% *
TRANSISTOR COMPLEMENT	One silicon field effect transistor and six silicon transistors.
BATTERY LIFE AND TYPE**	100 hours: 600 ohms or higher loads 80 hours: 150 ohms 50 hours: 50 ohms Battery: 1 Burgess type 4156 (22-1/2V) dry cell or equiv.
AC INPUT REQUIREMENTS	105-130 v a-c, 50 cps-400 cps at 6 ma approx. can be operated with 230 v a-c, 50-400 cps by using SKN6009A 230/117 VAC Adapter Cable Kit (optional).
FILTER (1 KC DISTORTION ANALYZER) CHARACTERISTICS	frequency accuracy = ±5% 1 kc rejection = more than 50 db input resistance = 600 ohms (approx.)
OPERATING TEMPERATURE	0° to +50°C (32°F to 122°F)
DIMENSIONS	10-1/4 x 6-1/2" x 5-3/4" (approx.)
WEIGHT	7-3/4 pounds

*50 cps to 200 kc with 150 ohm or higher load at 1.5 v rms maximum and 50 ohm load at 1 v rms maximum.

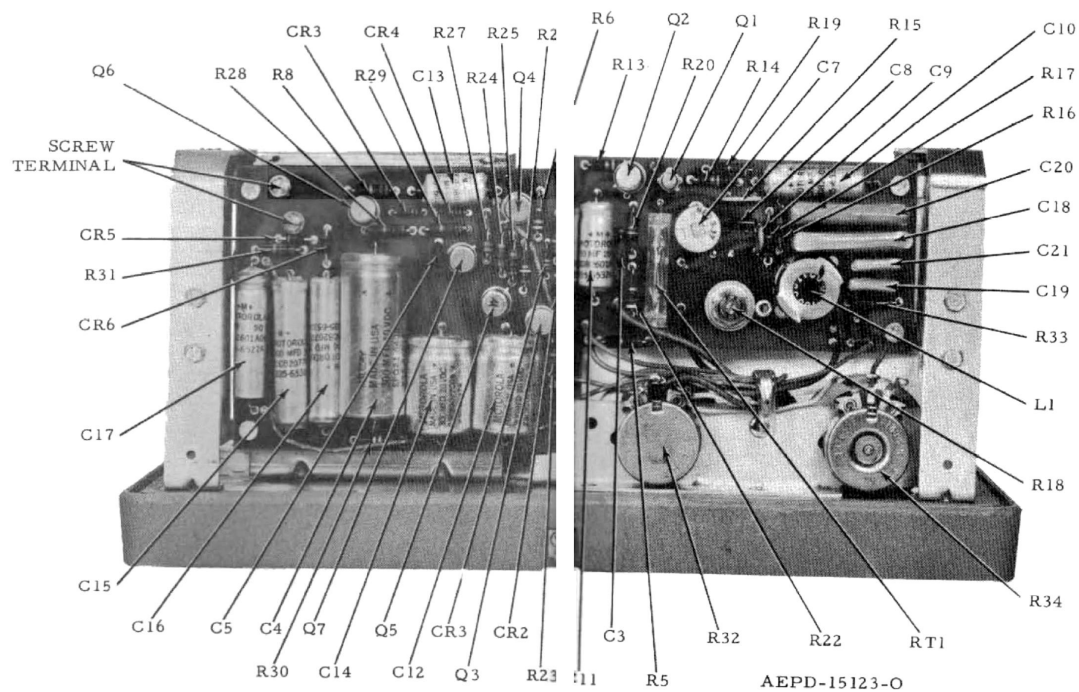
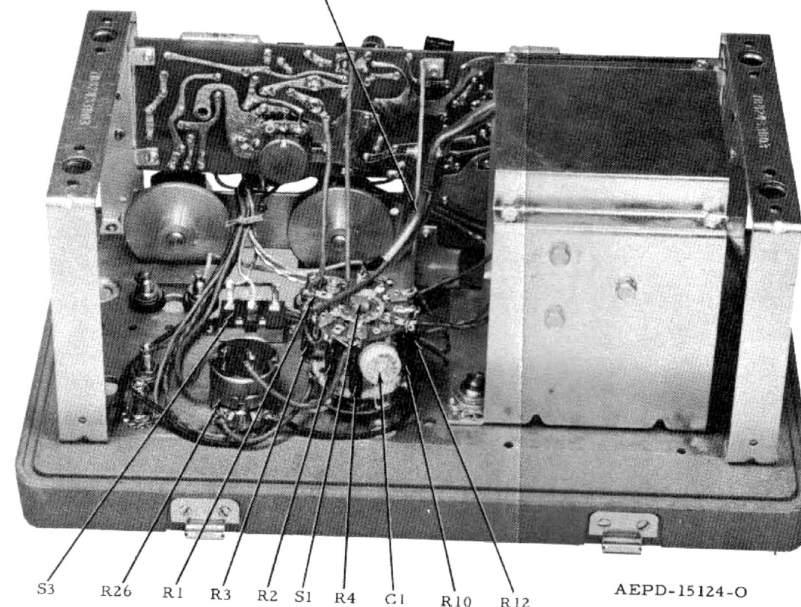
**Based on discharge time of 4 hours per day at room temperature.

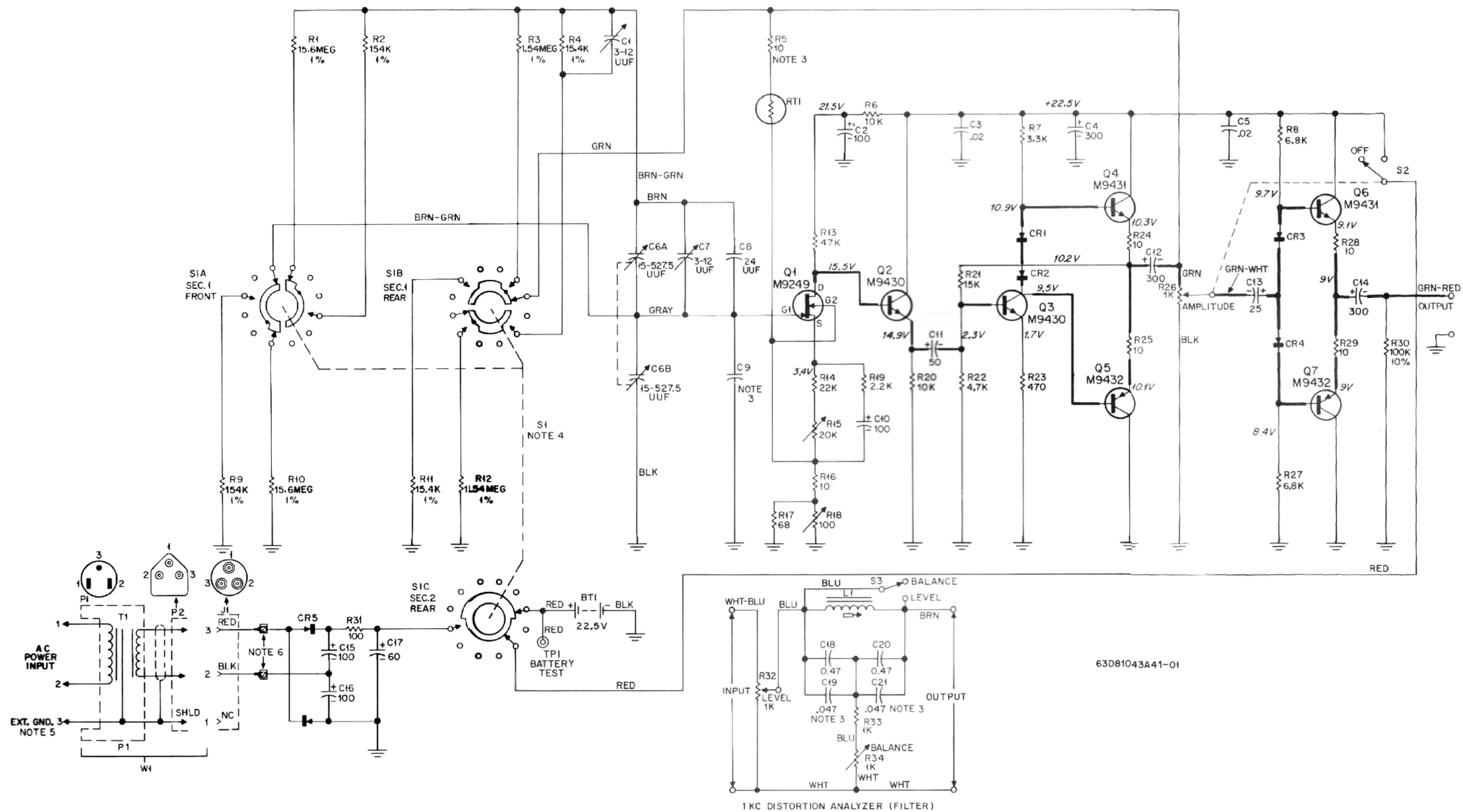
SPECIFICATIONS SUBJECT TO CHANGE WITHOUT NOTICE

BATTERY LEADS AEPD-15125-O



BATTERY LEADS





REFERENCE SYMBOL	MOTOROLA PART NO.	DESCRIPTION
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PARTS LIST

SLN6211A Audio Oscillator Kit

EPD-15282-A

C1, 7	20K848635	<u>CAPACITOR, variable:</u> 3-12 uuf; NP0
C6	19C83731D01	2 section; consist of:
C6A		15-527.5 uuf; 350 v
C6B		15-527.5 uuf; 350 v
C2, 15, 16	23C82077C01	<u>CAPACITOR, fixed:</u> 100 uf +150-10%; 35 v
C3, 5	21B82428B01	.02 uf +60-40%; 100 v
C4	23C82077C14	300 uf +150-10%; 40 v
C8	21K859937	24 uuf ±5%; 500 v
C9		(factory selected)
C10	23D82601A21	100 uf +100-0%; 10 v
C11	23D82601A05	50 uf +150-10%; 25 v
C12, 14	23C82077C05	300 uf +150-10%; 20 v
C13	23D82601A26	25 uf +150-10%; 20 v
C17	23D82601A29	60 uf +150-10%; 50 v
C18, 20	8D82905G06	0.47 uf ±10%; 50 v
C19, 21	8D82905G03	.047 uf ±10%; 50 v
CR1, 2, 3, 4	48C82392B03	<u>SEMICONDUCTOR DEVICE,</u> <u>diode; (NOTE)</u>
CR5, 6	48C82466H03	silicon
J1	9B82137E01	<u>CONNECTOR, receptacle:</u> female; 3 contact
L1	24V80902A88	<u>REACTOR:</u> tunable
Q1	48R869429	<u>TRANSISTOR: (NOTE)</u> F. E. T.; type M9429
Q2, 3	48R869430	N-P-N; type M9430
Q4, 6	48K869431	N-P-N; type M9431
Q5, 7	48R869432	P-N-P; type M9432
R1, 10	6D82475B67	<u>RESISTOR, fixed: ±5%; 1/2 w;</u> unl stated 15.6 meg ±1%
R2, 9	6D82672B46	154K ±1%
R3, 12	6D82475B66	1.54 meg ±1%
R4, 11	6D82672B45	15.4K ±1%
R5, 16, 24, 25, 28, 29	6S114018	10
R6, 20	6S5556	10K
R7	6S2003	3.3K
R8, 27	6S2001	6.8K
R13	6S5772	47K
R14	6S6480	22K
R15	18C82567D01	variable: 20K ±20%; 1/8 w
R17	6S400424	68
R18	18C82676B01	variable: 100 ±20%; 0.2 w
R19	6R2028	2.2K
R21	6S5726	15K
R22	6S3924	4.7K
R23	6S400812	470
R26	18C82810C06	1K ±30%; incl. S2
R30	6S6031	100K
R31	6S6408	100
R32, 34	18D82515B01	1K
R33	6S400459	1.5K
RT1	6B83728D01	<u>THERMISTOR:</u> 1.2K ±20% @ 25°C
S1	40C83730D01	<u>SWITCH,</u> rotary; 3 section; special type
S2		(spst; p/o R26)
S3	40A11589	slide; spdt
TP1	9K833983	<u>TEST POINT:</u> single contact; RED